CMOS Digital Integrated Circuits Silicon Monolithic

TDS4A212MX,TDS4B212MX

1. Functional Description

1-32Gbps 1-Lane Two Differential Channel, 2:1 Mux/1:2 De-Mux

2. General

TDS4A212MX, TDS4B212MX are high-speed differential channel multiplexer(Mux)/demultiplexer(De-Mux) switches. These devices are designed to support up to 32Gbps high-speed differential interfaces such as PCIe® 5.0, CXL 2.0, USB4[®] Version 2.0, ThunderboltTM 4, DisplayPortTM 2.0.

TDS4A212MX and TDS4B212MX have different pin assignment. TDS4B212MX has an optimized pin assignment to achieve high frequency performance, while TDS4A212MX's pin assignment is easy to use for board layout.

The A Port (An+, An-) is connected to either the B Port (Bn+, Bn-) or C Port (Cn+, Cn-), which is determined by the combination of both the select (SEL) and output enable (OE). When the output enable (OE) is held at a highlevel, the switches are open (high-impedance state), regardless of the state of the select, thus these devices have lower consumption current.

The devices are designed to operate in temperatures from -40 °C to 105 °C and can be used for application including industrial use cases.

3. Features

- (1)Operating voltage: $V_{CC} = 1.6$ to 3.6 V
- Operating temperature : $T_{\rm opr}$ = -40 to 105 $^{\circ}\text{C}$ (2)
- Low current consumption For active mode (Typ.) $: I_{ope} = 60 \ \mu A$, (3)

For standby mode (Max) : I_{STB} = 10 μ A

(4)	-3-dB Bandwidth (differential) BW _(Diff) (Typ.) :	TDS4B212MX = 27.5 GHz
		TDS4A212MX = 26.2 GHz
(5)	Differential insertion Loss DDIL (Typ.) :	TDS4B212MX = -1.4 dB @ f = 16 GHz
		TDS4A212MX = -1.9 dB @ f = 16 GHz
(6)	Differential return Loss DDRL (Typ.) :	TDS4B212MX = -16 dB @ f = 16 GHz
		TDS4A212MX = -18 dB @ f = 16 GHz
(7)	Differential Off Isolation DDOIRR (Typ.) :	TDS4B212MX = -14 dB @ f = 16 GHz
		TDS4A212MX = -11 dB @ f = 16 GHz
(8)	Differential Crosstalk DDXT (Typ.) :	TDS4B212MX = -36 dB @ f = 16 GHz
		TDS4A212MX = -30 dB @ f = 16 GHz

(9)Package: XQFN16

4. Interfaces

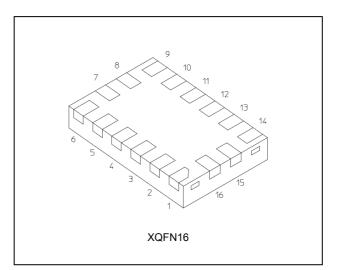
· PCIe 5.0/4.0	\cdot Thunderbolt 4/3
· CXL 2.0/1.0	· DisplayPort 2.0/1.4
\cdot USB4 Version 2.0, Gen3/Gen2	\cdot USB 3.2 Gen 2/Gen 1
\cdot SAS 3.0	

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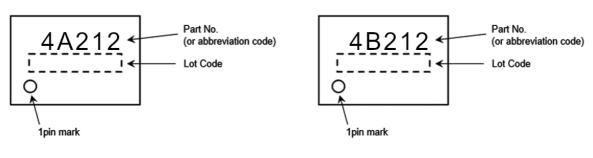
Start of commercial production 2024-05

5. Packaging



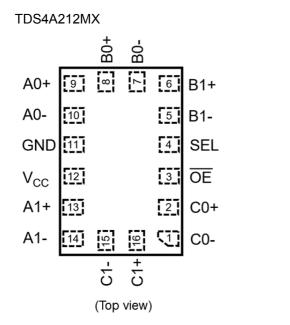
6. Marking

TDS4A212MX



TDS4B212MX

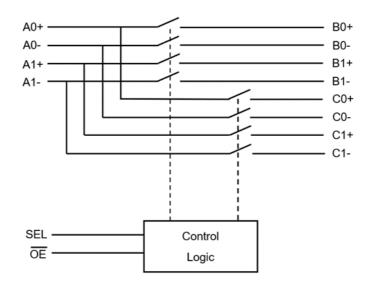
7. Pin Assignment



TDS4B212MX B0+ ВQ ~ ø 6 A0-9 C0-A0+ 10 5 C0+ GND 11 V_{CC} 4 SEL 12 3 ŌĒ A1+ 13 2 B1+ ত্র 15 16 A1-14 B1-C1+ ά

(Top view)

8. Block Diagram



9. Principle of Operation

9.1. Truth Table

Inputs OE	Inputs SEL	Function					
L	L	An+ port = Bn+ port, An- port = Bn- port	(n=0,1)				
L	Н	An+ port = Cn+ port, An- port = Cn- port	(n=0,1)				
Н	_	An, Bn, Cn port Disconnect	(n=0,1)				

—: Don't care

10. Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	-0.5 to 4.0	V
Input voltage (OE, SEL)	V _{IN}	-0.5 to 4.0	V
Switch I/O voltage	Vs	-0.5 to 2.5	V
Switch I/O current	۱ _S	32	mA
Power dissipation	P _D	180	mW
V _{CC} /ground current	I _{CC} /I _{GND}	±50	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

11. Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	1.6 to 3.6	V
Input voltage (OE, SEL)	V _{IN}	0 to 3.6	V
Signal pins differential voltage.	V _{I/O(Diff)}	0 to 1.8	V
Signal pins common mode voltage.	V _{I/O(Com)}	0 to 2.0	V
Operating temperature	T _{opr}	-40 to 105	°C
Input rise and fall times	dt/dv	0 to 10	ns/V

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused control inputs must be tied to either V_{CC} or GND.

12. Electrical Characteristics

12.1. DC Characteristics

12.1.1. DC Characteristics (Note) (Unless otherwise specified, $T_a = -40$ to 85 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Unit
High-level input voltage (\overline{OE} , SEL)	V _{IH}	_	1.65 to 3.6	$0.65 \times V_{CC}$	—	—	V
Low-level input voltage (OE, SEL)	V _{IL}	l	1.65 to 3.6		—	$0.35 \times V_{CC}$	V
Input leakage current (OE, SEL)	I _{IN}	V _{IN} = 0 to 3.6 V	1.65 to 3.6	_	—	±1	μA
Switch OFF-state leakage current	I _{SZ}	$\frac{V_{IS}}{OE} = 0 \text{ to } 2.5 \text{ V},$ $\frac{V_{IS}}{OE} = V_{CC}$	1.65 to 3.6	_	—	±3	μA
ON-resistance	R _{ON}	V _{IS} = 0 V, I _{IS} = 8 mA (TDS4A212)	3.0		—	8.4	Ω
		V _{IS} = 0 V, I _{IS} = 8 mA (TDS4B212)	3.0	_	—	7.9	
		V _{IS} = 2 V, I _{IS} = 8 mA	3.0	_	—	15	
Standby current	I _{STB}	$\frac{V_{IN}}{OE} = V_{CC} \text{ or GND},$	3.6	—	—	10	μA
Current consumption	I _{ope}	$\frac{V_{IN}}{OE} = V_{CC} \text{ or GND},$ $\overline{OE} = GND$	3.6	_	60	150	μA

Note : All typical values are at $T_a = 25$ °C.

12.1.2. DC Characteristics (Note) (Unless otherwise specified, $T_a = -40$ to 105 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Unit
High-level input voltage (\overline{OE} , SEL)	V _{IH}	—	1.65 to 3.6	$0.65 \times V_{CC}$	_	—	V
Low-level input voltage (OE, SEL)	V _{IL}	_	1.65 to 3.6			$0.35 \times V_{CC}$	V
Input leakage current (OE, SEL)	I _{IN}	V _{IN} = 0 to 3.6 V	1.65 to 3.6	_		±1	μA
Switch OFF-state leakage current	I _{SZ}	$\frac{V_{IS}}{OE} = 0 \text{ to } 2.5 \text{ V},$ $\overline{OE} = V_{CC}$	1.65 to 3.6			±4	μA
ON-resistance	R _{ON}	V _{IS} = 0 V, I _{IS} = 8 mA (TDS4A212)	3.0	_	_	8.9	Ω
		V _{IS} = 0 V, I _{IS} = 8 mA (TDS4B212)	3.0	—	_	8.4	
		V _{IS} = 2 V, I _{IS} = 8 mA	3.0	_	—	16	
Standby current	I _{STB}	$\frac{V_{IN}}{OE} = V_{CC} \text{ or GND},$ $\frac{V_{IN}}{OE} = V_{CC}$	3.6	—	_	10	μA
Current consumption	I _{ope}	$\frac{V_{IN}}{OE} = V_{CC} \text{ or GND},$ $\overline{OE} = GND$	3.6	_	60	150	μA

Note: All typical values are at $T_a = 25$ °C.

12.2. High frequency characteristics (Note) (Unless otherwise specified, V_{CC} = 1.6 to 3.6 V)

12.2.1. TDS4A212MX

Characteristics	Symbol	Note	Test Condition		Тур.	Unit				
-3-dB Bandwidth (differential)	BW _(Diff)	(Note 1)	R_L = 50 Ω , See Fig. 13.1		26.2	GHz				
Differential insertion loss	DDIL	(Note 1)	R _L = 50 Ω	f = 2.5 GHz	-0.7	dB				
			See Fig. 13.1	f = 4.0 GHz	-0.8					
				f = 5.0 GHz	-0.9]				
				f = 8.0 GHz	-1.0					
				f = 10.0 GHz	-1.1					
				f = 12.8 GHz	-1.4]				
				f = 16.0 GHz	-1.9					
Differential return loss	DDRL	(Note 1)	R _L = 50 Ω	f = 2.5 GHz	-18	dB				
			See Fig. 13.1	f = 4.0 GHz	-19]				
				f = 5.0 GHz	-15					
				f = 8.0 GHz	-14]				
				f = 10.0 GHz	-17					
				f = 12.8 GHz	-17					
								f = 16.0 GHz	-18	
Differential OFF isolation	DDOIRR	(Note 1)	R _L = 50 Ω	f = 2.5 GHz	-25	dB				
	See Fig. 13.2	See Fig. 13.2	f = 4.0 GHz	-22						
				f = 5.0 GHz	-20					
				f = 8.0 GHz	-19]				
				f = 10.0 GHz	-17					
				f = 12.8 GHz	-12]				
				f = 16.0 GHz	-11					
Differential Crosstalk	DDXT	(Note 1)		f = 2.5 GHz	-40	dB				
			See Fig. 13.3, 13.4	f = 4.0 GHz	-37]				
				f = 5.0 GHz	-36					
				f = 8.0 GHz	-34]				
				f = 10.0 GHz	-32]				
				f = 12.8 GHz	-31					
				f = 16.0 GHz	-30]				

Note: All typical values are at $T_a = 25$ °C.

Note 1: Parameter guaranteed by design.

12.2.2. TDS4B212MX

Characteristics	Symbol	Note	Test Condition	est Condition		Unit	
-3-dB Bandwidth (differential)	BW _(Diff)	(Note 1)	R _L = 50 Ω, See Fig. 13.1		27.5	GHz	
Differential insertion loss	loss DDIL (Note	(Note 1)	R _L = 50 Ω	f = 2.5 GHz	-0.7	dB	
			See Fig. 13.1	f = 4.0 GHz	-0.8	1	
				f = 5.0 GHz	-0.8	1	
				f = 8.0 GHz	-0.9]	
				f = 10.0 GHz	-0.9]	
				f = 12.8 GHz	-1.2		
				f = 16.0 GHz	-1.4		
Differential return loss	DDRL	(Note 1)		f = 2.5 GHz	-20	dB	
			See Fig. 13.1	f = 4.0 GHz	-18		
				f = 5.0 GHz	-17		
				f = 8.0 GHz	-15]	
				f = 10.0 GHz	-20]	
				f = 12.8 GHz	-17		
				f = 16.0 GHz	-16]	
Differential OFF isolation	DDOIRR	(Note 1)	R _L = 50 Ω	f = 2.5 GHz	-25	dB	
			See Fig. 13.2	f = 4.0 GHz	-21		
				f = 5.0 GHz	-20		
					f = 8.0 GHz	-17]
			f = 10.0 GHz	-16]		
				f = 12.8 GHz	-17]	
				f = 16.0 GHz	-14		
Differential Crosstalk	DDXT	(Note 1)		f = 2.5 GHz	-68	dB	
			See Fig. 13.3, 13.4	f = 4.0 GHz	-60]	
				f = 5.0 GHz	-56]	
				f = 8.0 GHz	-48]	
				f = 10.0 GHz	-44]	
				f = 12.8 GHz	-39]	
				f = 16.0 GHz	-36]	

Note: All typical values are at $T_a = 25$ °C. Note 1: Parameter guaranteed by design.

12.3. Switching Characteristics (Unless otherwise specified, Ta = 25 °C)

12.3.1. TDS4A212MX

Characteristics	Symbol	Note	Test Condition	V _{CC} (V)	Тур.	Max	Unit
Propagation delay time	t _{PLH} /t _{PHL}	(Note 1)	R _L = 50 Ω, f = 10 GHz See Fig. 13.1, 13.7	3.3	33	_	ps
Output skew (bit to bit)	t _{SK(b)}	(Note 1)	R _L = 50 Ω, f = 10 GHz See Fig. 13.1, 13.8	3.3	6	_	ps
Output skew (channel to channel)	t _{SK(CH)}	(Note 1)	R _L = 50 Ω, f = 10 GHz See Fig. 13.1, 13.7	3.3	6	—	ps

Note 1: Parameter guaranteed by design.

12.3.2. TDS4B212MX

Characteristics	Symbol	Note	Test Condition	V _{CC} (V)	Тур.	Max	Unit
Propagation delay time	t _{PLH} /t _{PHL}	(Note 1)	R _L = 50 Ω, f = 10 GHz See Fig. 13.1, 13.7	3.3	30	—	ps
Output skew (bit to bit)	t _{SK(b)}	(Note 1)	R _L = 50 Ω, f = 10 GHz See Fig. 13.1, 13.8	3.3	4	—	ps
Output skew (channel to channel)	t _{SK(CH)}	(Note 1)	R _L = 50 Ω, f = 10 GHz See Fig. 13.1, 13.7	3.3	2	_	ps

Note 1: Parameter guaranteed by design.

12.4. Timing characteristics

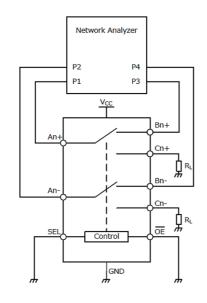
12.4.1. Timing characteristics (Unless otherwise specified, $T_a = -45$ to 85 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Unit
Start-up time.	t _{sup}	See Fig. 13.5	1.65 to 3.6	_	—	100	μS
Turn-ON time (SEL to Output)	t _{on}	$R_L = 50 \Omega$, $C_L = 5 pF$ See Fig. 13.5	1.65 to 3.6	_	—	180	ns
Turn-ON time (\overline{OE} to Output)			1.65 to 3.6		_	100	μS
Turn-OFF time (SEL to Output)	t _{off}	$R_L = 50 \Omega$, $C_L = 5 pF$ See Fig. 13.5	1.65 to 3.6	_	_	18	ns
Turn-OFF time (\overline{OE} to Output)			1.65 to 3.6	_	—	21	
Break before make	TBBM	R _L = 50 Ω, C _L = 5 pF See Fig. 13.6	1.65 to 3.6	55	—	160	ns

12.4.2. Timing characteristics (Unless otherwise specified, $T_a = -45$ to 105 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Unit
Start-up time.	t _{sup}	See Fig. 13.5	1.65 to 3.6	_	_	110	μS
Turn-ON time (SEL to Output)	t _{on}	R_L = 50 Ω, C_L = 5 pF See Fig. 13.5	1.65 to 3.6	_	_	180	ns
Turn-ON time (OE to Output)			1.65 to 3.6	_	_	110	μS
Turn-OFF time (SEL to Output)	t _{off}	R_L = 50 Ω, C_L = 5 pF See Fig. 13.5	1.65 to 3.6	_	—	20	ns
Turn-OFF time (\overline{OE} to Output)			1.65 to 3.6	_	_	25	
Break before make	TBBM	$R_L = 50 \Omega$, $C_L = 5 pF$ See Fig. 13.6	1.65 to 3.6	55	—	160	ns

13. AC Electrical Test Circuit (Fig)

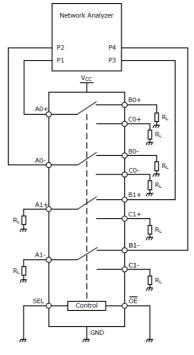


R_L = 50 Ω

All unused ports are connected to GND through 50 Ω pull-down resistors. This figure is an example showing how to measure An and Bn.

Fig. 13.1 -3-dB Bandwidth(differential), Differential insertion loss,Differential return loss, Propagation delay time,

Output skew (channel to channel, bit to bit)

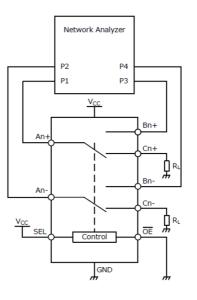


 $R_L = 50 \ \Omega$

All unused ports are connected to GND through 50 Ω pull-down resistors.

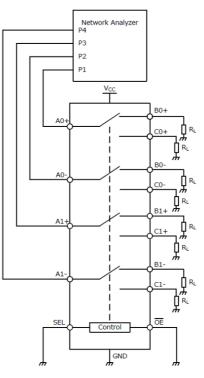
This figure is an example showing how to measure A0 and B1.

Fig. 13.3 Differential Far-end crosstalk



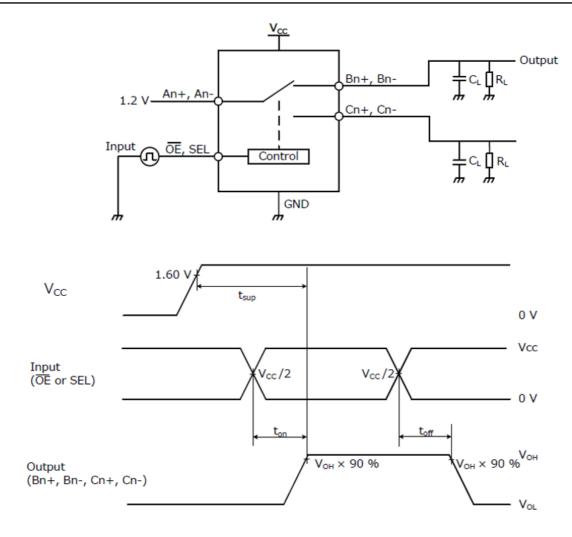
 $\rm R_L$ = 50 Ω All unused ports are connected to GND through 50 Ω pull-down resistors. This figure is an example showing how to measure An and Bn.

Fig. 13.2 Differential OFF isolation



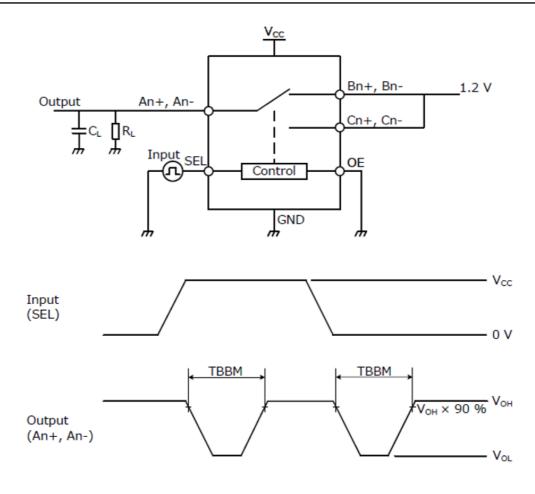
 $R_L=50~\Omega$ All unused ports are connected to GND through $50~\Omega$ pull-down resistors. This figure is an example showing how to measure A0 and A1.

Fig. 13.4 Differential Near-end crosstalk

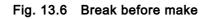


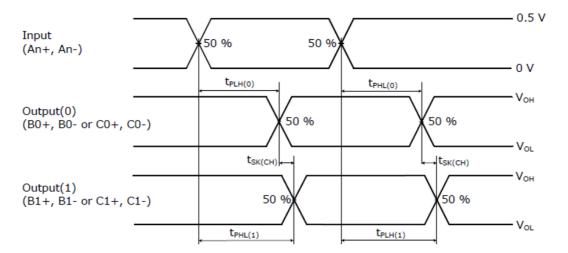
$$R_L = 50 \Omega, C_L = 5 pF$$

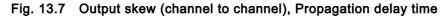
Fig. 13.5 Start-up, Turn-ON and Turn-OFF time



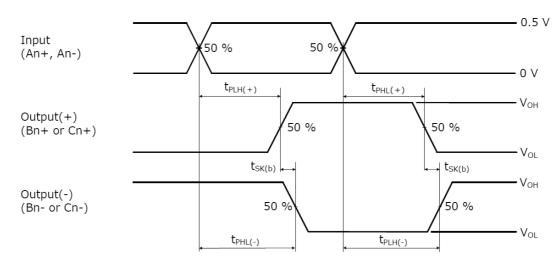
 $R_L = 50 \Omega, C_L = 5 pF$

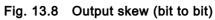






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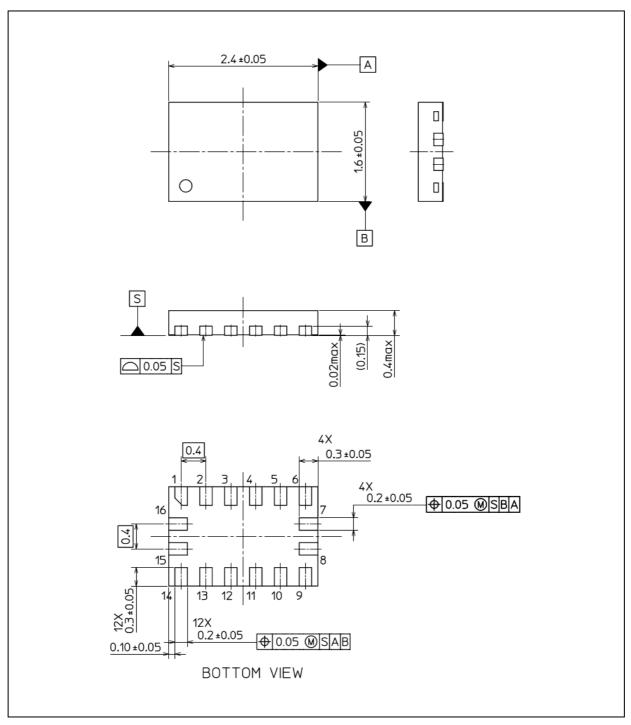




TDS4A212MX,TDS4B212MX

Package Dimensions

Unit: mm



Weight: 3.9 mg (typ.)

Package Name(s)

Nickname: XQFN16

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